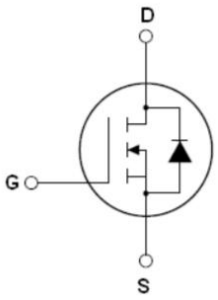
N-Channel Super Junction Power MOSFET Ⅳ

General Description

The series of devices use advanced trench gate super junction technology and design to provide ultra-low $R_{DS(ON)}$ and low gate charge and With a rapid recovery body diode.This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, industrial power applications,Fast charger, new energy vehicle charging pile, on-board OBC etc.

$V_{DS\ min@Tjmax}$	710	V
$R_{DS(ON)TYP.}$	30	mΩ
I_D	70	A
Qg	125	nC



Features

- ●New technology for high voltage device
- ●Ultra low on-resistance and ultra low conduction losses
- ●Ultra Low Gate Charge cause lower driving requirements
- ●Diode reverse recovery speed is super fast
- ●100% Avalanche Tested and 100% T_{rr} Tested
- ●High reliability
- ●ROHS compliant

Application

- ● Power factor correction（PFC）
- ● Switched mode power supplies(SMPS)
- ● Uninterruptible Power Supply（UPS）
- ● On-board charger(OBC)

✧ **Intrinsic fast-recovery body diode**

Schematic diagram

Package Marking And Ordering Information

Device	Device Package	Marking
NCE65NF036T4	TO-247-4L	NCE65NF036T4

TO-247-4L

Table 1. Absolute Maximum Ratings (T_C=25℃)

Parameter	Symbol	Value	Unit
Drain-Source Voltage (V_{GS}=0V）	V_{DS}	650	V
Gate-Source Voltage (V_{DS}=0V) ,AC (f>1 Hz)	V_{GS}	±30	V
Gate-Source Voltage (V_{DS}=0V) ,DC	V_{GS}	±20	V
Continuous Drain Current at Tc=25°C	$I_{D\ (DC)}$	70	A
Continuous Drain Current at Tc=100°C	$I_{D\ (DC)}$	49	A
Pulsed drain current (Note 1)	$I_{DM\ (pluse)}$	210	A
Maximum Power Dissipation(Tc=25℃) Derate above 25°C	P_D	488 3.25	W W/°C
Single pulse avalanche energy (Note 2)	E_{AS}	1024	mJ
Single pulse avalanche current (Note 2)	I_{AS}	16	A
Repetitive Avalanche energy ， t_{AR} limited by T_{jmax} (Note 1)	E_{AR}	0.9	mJ

Reverse diode dv/dt， V_{DS} ≤480 V,I_{SD}<I_D	dv/dt	50	V/ns
Drain Source voltage slope， V_{DS} ≤480 V	dv/dt	50	V/ns
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55...+175	°C

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance，Junction-to-Case（Maximum）	R_{thJC}	0.31	°C /W
Thermal Resistance，Junction-to-Ambient （Maximum）	R_{thJA}	62	°C /W

Table 3. Electrical Characteristics (TA=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=1mA	650			V
Zero Gate Voltage Drain Current(Tc=25℃)	I_{DSS}	V_{DS}=650V,V_{GS}=0V			10	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I_{DSS}	V_{DS}=650V,V_{GS}=0V			400	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V			±200	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=3mA	3	4	5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=35A		30	36	mΩ
Dynamic Characteristics						
Gate Resistance	Rg	F=1MHZ, D-S short		4		Ω
Input Capacitance	C_{lss}	V_{DS}=50V,V_{GS}=0V, F=1MHz		7727		pF
Output Capacitance	C_{oss}			263		pF
Reverse Transfer Capacitance	C_{rss}			25.1		pF
Total Gate Charge	Q_g	V_{DS}=400V,I_D=40A,V_{GS}=10V		125	135	nC
Gate-Source Charge	Q_{gs}			57		nC
Gate-Drain Charge	Q_{gd}			34		nC
Gate plateau voltage	Vgp			6.5		V
Switching times						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=380V,I_D=40A, R_G=4Ω,V_{GS}=10V		54		nS
Turn-on Rise Time	t_r			37		nS
Turn-Off Delay Time	$t_{d(off)}$			127		nS
Turn-Off Fall Time	t_f			5		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I_{SD}	T_C=25°C			70	A
Pulsed-Source-drain current(Body Diode)	I_{SDM}				210	A
Forward on voltage	V_{SD}	Tj=25°C,I_{SD}=70A,V_{GS}=0V		1.0	1.2	V
Reverse Recovery Time	t_{rr}	Tj=25°C,I_F40A, di/dt=100A/μs		185		nS
Reverse Recovery Charge	Q_{rr}			1.6		uC
Peak reverse recovery current	I_{rrm}			16		A

Notes: 1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. Tj=25℃,VDD=50V,VG=10V, R_G=25Ω

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area

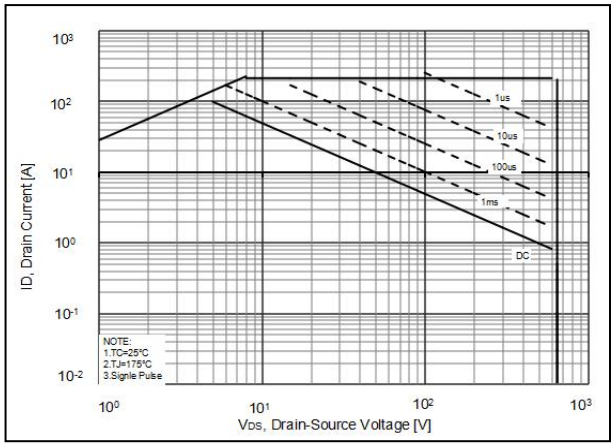


Figure2. Source-Drain Diode Forward Voltage

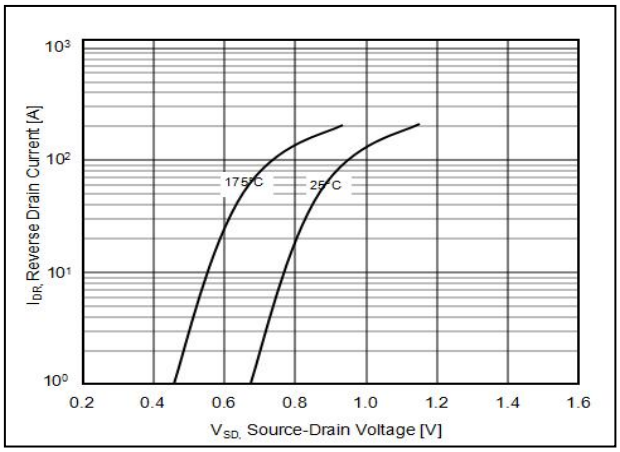


Figure3. Output characteristics（25℃）

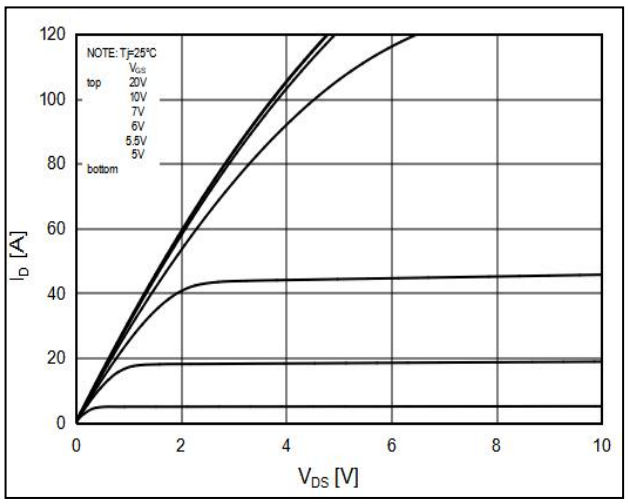


Figure4. Transfer characteristics

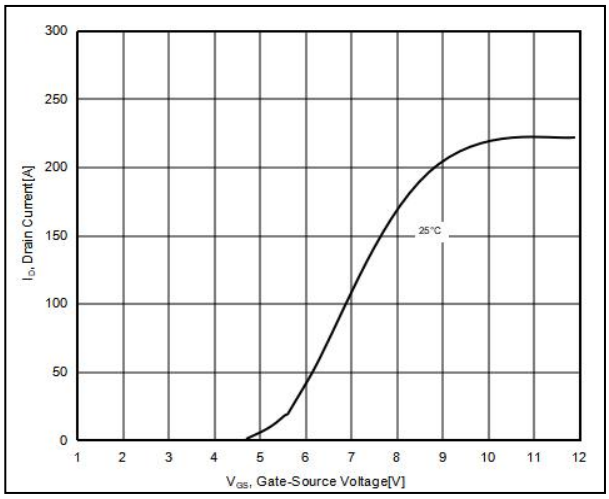


Figure5. Static drain-source on resistance

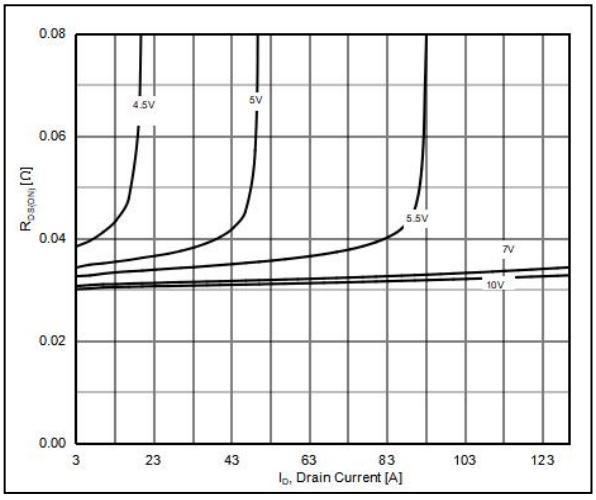


Figure6. $R_{DS(ON)}$ vs Junction Temperature

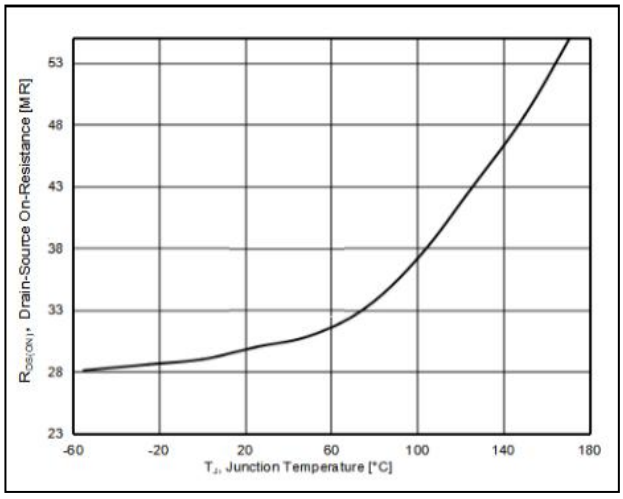


Figure7. BV_{DSS} vs Junction Temperature

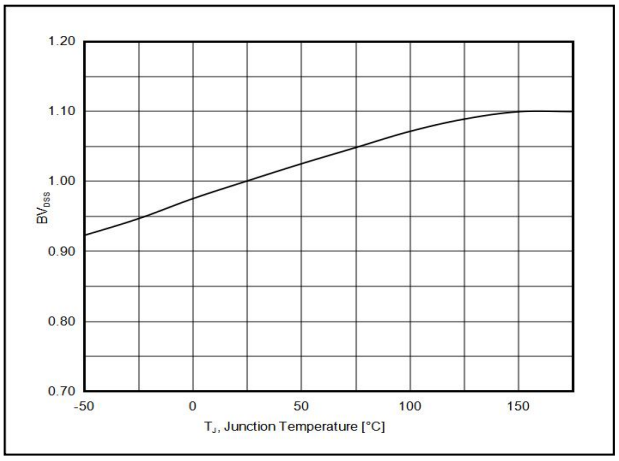


Figure8. Maximum I_D vs Junction Temperature

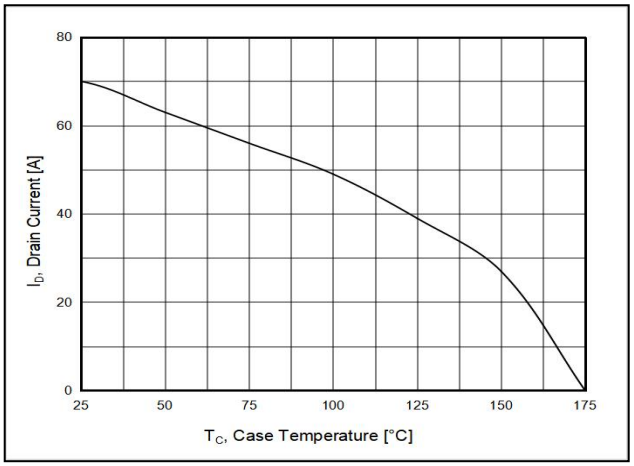


Figure9. Gate charge waveforms

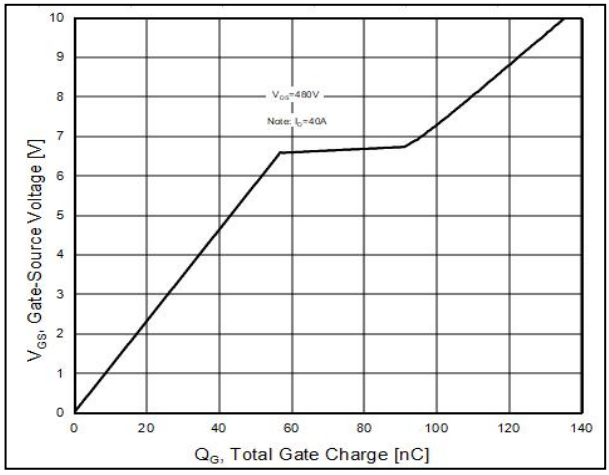


Figure10. Capacitance

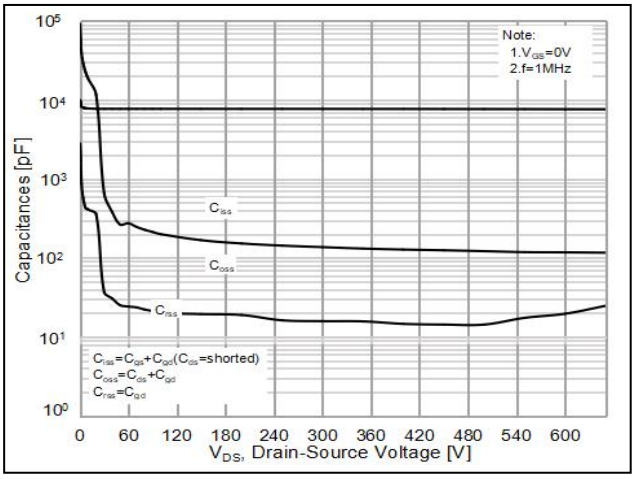
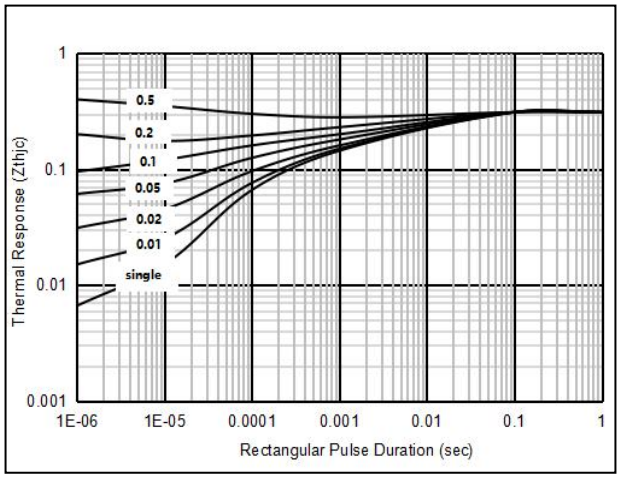
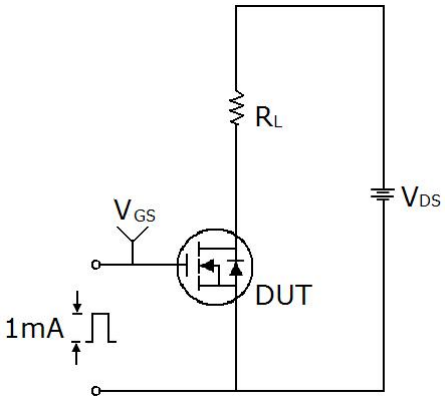


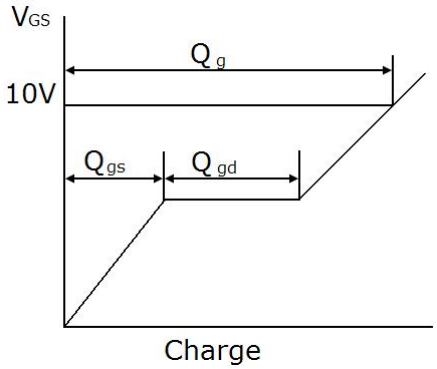
Figure11. Transient Thermal Impedance



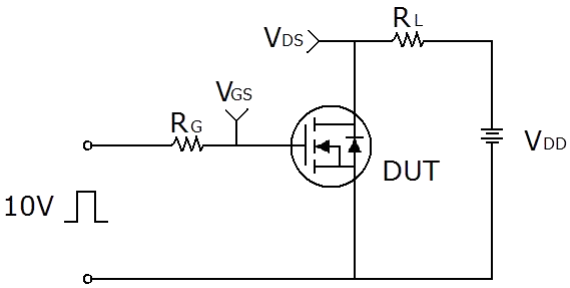
Test circuit

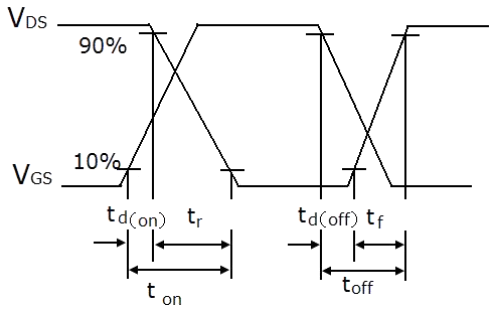
1）Gate charge test circuit & Waveform



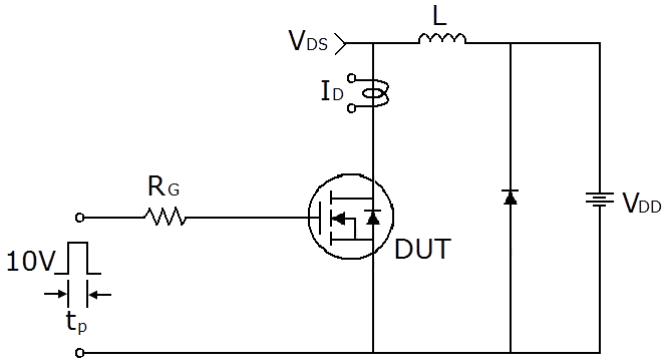


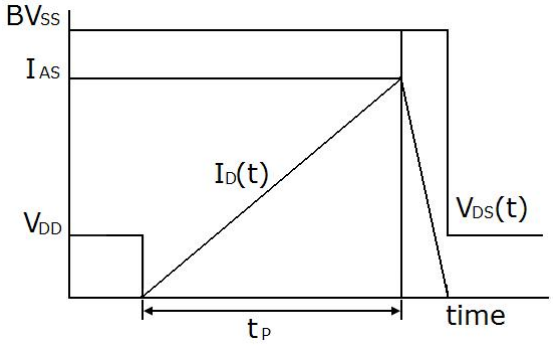
2）Switch Time Test Circuit：



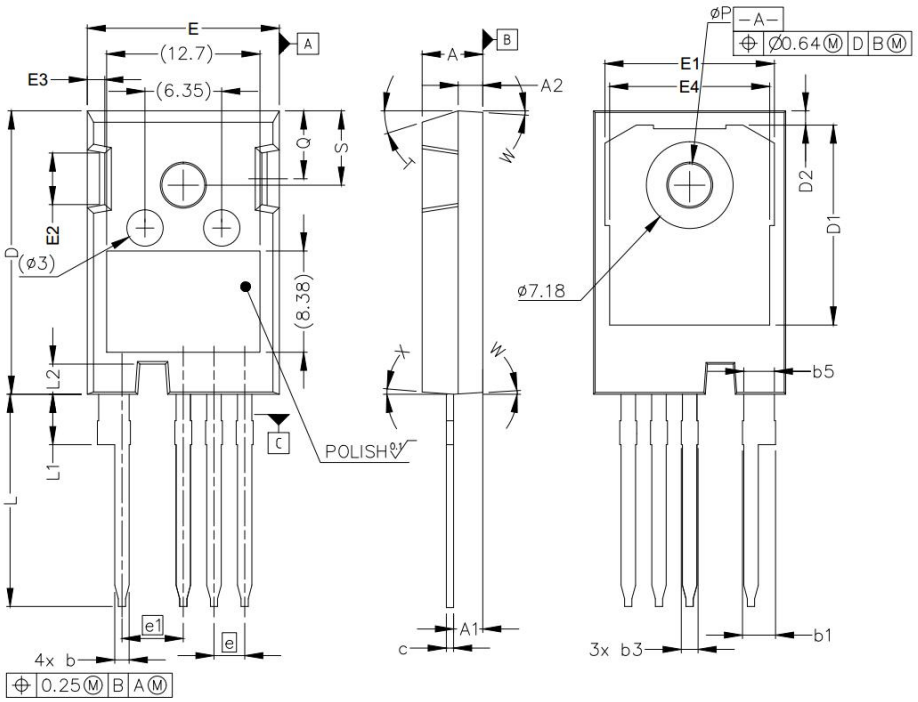


3）Unclamped Inductive Switching Test Circuit & Waveforms





TO-247-4L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	0.19	0.21
A1	2.29	2.54	0.09	0.10
A2	1.91	2.16	0.08	0.09
b	1.07	1.33	0.04	0.05
b1	2.39	2.94	0.09	0.12
b3	1.07	1.60	0.04	0.06
b5	2.39	2.69	0.09	0.11
c	0.55	0.68	0.02	0.03
D	23.30	23.60	0.92	0.93
D1	16.25	17.65	0.64	0.69
D2	0.95	1.25	0.04	0.05
E	15.75	16.13	0.62	0.64
E1	13.10	14.15	0.52	0.56
E2	3.68	5.10	0.14	0.20
E3	1.00	1.90	0.04	0.07
E4	12.38	13.43	0.49	0.53
e	2.54 BSC		0.1 BSC	
e1	5.08 BSC		0.2 BSC	
L	17.31	17.82	0.68	0.70
L1	3.97	4.37	0.16	0.17
L2	2.35	2.65	0.09	0.10
ΦP	3.51	3.65	0.14	0.14
Q	5.49	6.00	0.22	0.24
S	6.04	6.30	0.24	0.25
T	17.5° REF.			
W	3.5° REF.			
X	4.0° REF.			

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